



TISP61089D, TISP61089SD, TISP61089AD,
TISP61089ASD

DUAL FORWARD-CONDUCTING P-GATE THYRISTORS
PROGRAMMABLE OVERVOLTAGE PROTECTORS

TISP61089 Gated Protector Series

Overvoltage Protection for Negative Rail SLICs

- Dual Voltage-Tracking Protectors
- '61089 for Battery Voltages to -75 V
 - '61089A for Battery Voltages to -100 V
 - Low Gate Triggering Current < 5 mA
 - High Holding Current > 150 mA

Rated for GR-1089-CORE and K.44 Impulses

Impulse Wave Shape		I _{PPSM} A
Voltage	Current	
2/10	2/10	120
10/700	5/310	40
10/1000	10/1000	30

2/10 Overshoot Voltage Specified

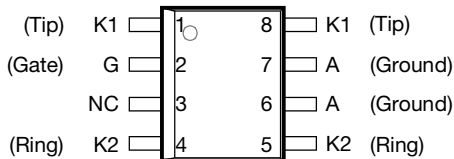
Element	I _{pp} = 100 A, 2/10
	V
Diode	8
SCR	12

Package Options

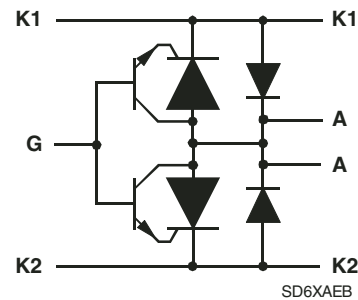
- Surface Mount 8-pin Small-Outline
- Line Feed-Thru Connection (D)
- Shunt Version Connection (SD)

..... UL Recognized Components

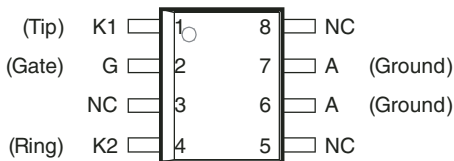
D Package Top View and Device Symbol for Feed-Thru Pin-Out



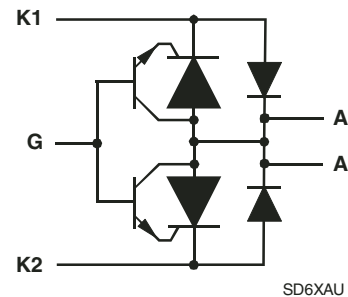
NC - No internal connection
Terminal typical application names shown in parenthesis
MD6XBDA



D Package Top View and Device Symbol for Shunt (SD) Pin-Out



NC - No internal connection
Terminal typical application names shown in parenthesis
MD6XBE



How To Order

Device	Package	Carrier	Order As	Device	Package	Carrier	Order As
TISP61089	D (Small-Outline)	R†	TISP61089DR-S	TISP61089A	D (Small-Outline)	R†	TISP61089ADR-S
		Tube	TISP61089D-S			Tube	TISP61089AD-S
TISP61089S	D (Small-Outline)	R†	TISP61089SDR-S	TISP61089AS	D (Small-Outline)	R†	TISP61089ASDR-S
		Tube	TISP61089SD-S			Tube	TISP61089ASD-S

† Carrier R is Embossed Tape Reeled

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*RoHS Directive 2002/95/EC Jan 27 2003 including Annex
NOVEMBER 1995 - REVISED JANUARY 2007
Specifications are subject to change without notice.
Customers should verify actual device performance in their specific applications.

TISP61089 Gated Protector Series

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Description

These '61089 parts are all dual forward-conducting buffered p-gate thyristor (SCR) overvoltage protectors. They are designed to protect monolithic SLICs (Subscriber Line Interface Circuits) against overvoltages on the telephone line caused by lightning, a.c. power contact and induction. The '61089 limits voltages that exceed the SLIC supply rail voltage. The '61089 parameters are specified to allow equipment compliance with Telcordia (formally Bellcore) GR-1089-CORE and ITU-T recommendations K.20, K.21 and K.45.

The SLIC line driver section is typically powered from 0 V (ground) and a negative (battery) voltage. The protector gate is connected to this negative supply. This references the protection (clipping) voltage to the negative supply voltage. The protection voltage will then track the negative supply voltage and the overvoltage stress on the SLIC is minimized.

Positive overvoltages are clipped to ground by diode forward conduction. Negative overvoltages are initially clipped close to the SLIC negative supply rail value. If sufficient current is available from the overvoltage, then the protector SCR will switch into a low voltage on-state condition. As the overvoltage subsides the high holding current of '61089 SCR avoids d.c. latchup.

The '61089 is intended to be used with a series resistance of at least 25 Ω and a suitable overcurrent function for Telcordia compliance. Power fault conditions require a series overcurrent element which either interrupts or reduces the circuit current before the '61089 current rating is exceeded. For equipment compliant to ITU-T recommendations K.20 or K.21 or K.45 only, the series resistor value is set by the coordination requirements. For coordination with a 400 V limit GDT, a minimum series resistor value of 10 Ω is recommended.

The '61089 buffered gate design reduces the loading on the SLIC supply during overvoltages caused by power cross and induction. The regular pin-out for surface mount and through-hole packages is a feed through configuration. Connection to the SLIC is made via the '61089, Ring through pins 4 - 5 and Tip through pins 1 - 8. A non-feed-through surface mount (D) package is available. This shunt (SD) version pin-out does not make duplicate connections to pin 5 and pin 8 which increases package creepage distance from ground of the other connections from about 0.7 mm to over 3 mm. High voltage ringing SLICs, with battery voltages below -100 V and down to -155 V, can be protected by the TISP61089B device. Details of this device are in the TISP61089B data sheet.

Absolute Maximum Ratings, $-40\text{ }^{\circ}\text{C} \leq T_J \leq 85\text{ }^{\circ}\text{C}$ (Unless Otherwise Noted)

Rating	Symbol	Value	Unit	
Repetitive peak off-state voltage, $V_{GK} = 0$	61089 '61089A	V_{DRM}	-100 -120	V
Repetitive peak gate-cathode voltage, $V_{KA} = 0$	61089 '61089A	V_{GKRM}	-85 -120	V
Non-repetitive peak on-state pulse current (see Notes 1 and 2)				
10/1000 μs (Telcordia (Bellcore) GR-1089-CORE, Issue 2, February 1999, Section 4)		I_{PPSM}	30	A
5/320 μs (ITU-T K.20, K.21& K.45, K.44 open-circuit voltage wave shape 10/700 μs)			40	
1.2/50 μs (Telcordia (Bellcore) GR-1089-CORE, Issue 2, February 1999, Section 4)			100	
2/10 μs (Telcordia (Bellcore) GR-1089-CORE, Issue 2, February 1999, Section 4)			120	
Non-repetitive peak on-state current, $V_{GG} = -75\text{ V}$, 50 Hz to 60 Hz (see Notes 1 and 2)				
0.1 s		I_{TSM}	11	A
1 s			4.8	
5 s			2.7	
300 s			0.95	
900 s			0.93	
Non-repetitive peak gate current, 1/2 μs pulse, cathodes commoned (see Notes 1 and 2)		I_{GSM}	+40	A
Operating free-air temperature range		T_A	-40 to +85	$^{\circ}\text{C}$
Junction temperature		T_J	-40 to +150	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-40 to +150	$^{\circ}\text{C}$

NOTES: 1. Initially the protector must be in thermal equilibrium with $-40\text{ }^{\circ}\text{C} \leq T_J \leq 85\text{ }^{\circ}\text{C}$. The surge may be repeated after the device returns to its initial conditions. Gate voltage ranges are -20 V to -75 V for the '61089 and -20 V to -100 V for the '61089A.

2. The rated current values may be applied either to the Ring to Ground or to the Tip to Ground terminal pairs. Additionally, both terminal pairs may have their rated current values applied simultaneously (in this case the Ground terminal current will be twice the rated current value of an individual terminal pair). Above 85 $^{\circ}\text{C}$, derate linearly to zero at 150 $^{\circ}\text{C}$ lead temperature.

TISP61089 Gated Protector Series

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Recommended Operating Conditions

Component		Min	Typ	Max	Unit
C_G	Gate decoupling capacitor	100	220		nF
R_S	Series resistor for GR-1089-CORE first-level surge survival	25			Ω
	Series resistor for GR-1089-CORE first-level and second-level surge survival	40			Ω
	Series resistor for GR-1089-CORE intra-building port surge survival	8			Ω
	Series resistor for K.20, K.21 and K.45 coordination with a 400 V primary protector	10			Ω

Electrical Characteristics, $T_J = 25^\circ\text{C}$ (Unless Otherwise Noted)

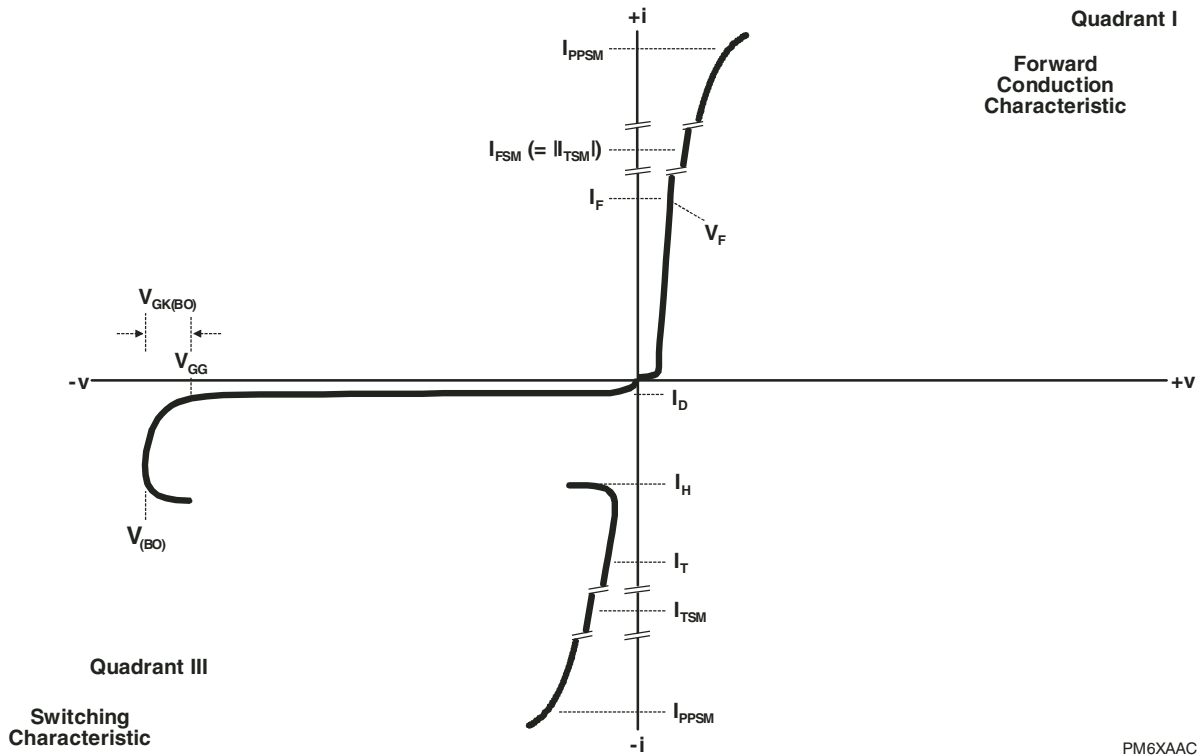
Parameter	Test Conditions	Min	Typ	Max	Unit
I_D Off-state current	$V_D = V_{DRM}, V_{GK} = 0$	$T_J = 25^\circ\text{C}$		-5	μA
		$T_J = 85^\circ\text{C}$		-50	μA
$V_{(BO)}$ Breakover voltage	2/10 μs , $I_{PP} = -56\text{ A}$, $R_S = 45\ \Omega$, $V_{GG} = -48\text{ V}$, $C_G = 220\text{ nF}$		-57		V
	2/10 μs , $I_{PP} = -100\text{ A}$, $R_S = 50\ \Omega$, $V_{GG} = -48\text{ V}$, $C_G = 220\text{ nF}$		-60		
	1.2/50 μs , $I_{PP} = -53\text{ A}$, $R_S = 47\ \Omega$, $V_{GG} = -48\text{ V}$, $C_G = 220\text{ nF}$		-60		
	1.2/50 μs , $I_{PP} = -96\text{ A}$, $R_S = 52\ \Omega$, $V_{GG} = -48\text{ V}$, $C_G = 220\text{ nF}$		-64		
$V_{GK(BO)}$ Gate-cathode impulse breakover voltage	2/10 μs , $I_{PP} = -56\text{ A}$, $R_S = 45\ \Omega$, $V_{GG} = -48\text{ V}$, $C_G = 220\text{ nF}$		9		V
	2/10 μs , $I_{PP} = -100\text{ A}$, $R_S = 50\ \Omega$, $V_{GG} = -48\text{ V}$, $C_G = 220\text{ nF}$		12		
	1.2/50 μs , $I_{PP} = -53\text{ A}$, $R_S = 47\ \Omega$, $V_{GG} = -48\text{ V}$, $C_G = 220\text{ nF}$		12		
	1.2/50 μs , $I_{PP} = -96\text{ A}$, $R_S = 52\ \Omega$, $V_{GG} = -48\text{ V}$, $C_G = 220\text{ nF}$		16		
V_F Forward voltage	$I_F = 5\text{ A}$, $t_W = 200\ \mu\text{s}$			3	V
V_{FRM} Peak forward recovery voltage	2/10 μs , $I_{PP} = 56\text{ A}$, $R_S = 45\ \Omega$, $V_{GG} = -48\text{ V}$, $C_G = 220\text{ nF}$		6		V
	2/10 μs , $I_{PP} = 100\text{ A}$, $R_S = 50\ \Omega$, $V_{GG} = -48\text{ V}$, $C_G = 220\text{ nF}$		8		
	1.2/50 μs , $I_{PP} = 53\text{ A}$, $R_S = 47\ \Omega$, $V_{GG} = -48\text{ V}$, $C_G = 220\text{ nF}$		8		
	1.2/50 μs , $I_{PP} = 96\text{ A}$, $R_S = 52\ \Omega$, $V_{GG} = -48\text{ V}$, $C_G = 220\text{ nF}$		12		
I_H Holding current	$I_T = -1\text{ A}$, $di/dt = 1\text{ A/ms}$, $V_{GG} = -48\text{ V}$	-150			mA
I_{GKS} Gate reverse current	$V_{GG} = V_{GK} = V_{GKRM}, V_{KA} = 0$	$T_J = 25^\circ\text{C}$		-5	μA
		$T_J = 85^\circ\text{C}$		-50	μA
I_{GT} Gate trigger current	$I_T = -3\text{ A}$, $t_{p(g)} \geq 20\ \mu\text{s}$, $V_{GG} = -48\text{ V}$			5	mA
V_{GT} Gate-cathode trigger voltage	$I_T = -3\text{ A}$, $t_{p(g)} \geq 20\ \mu\text{s}$, $V_{GG} = -48\text{ V}$			2.5	V
Q_{GS} Gate switching charge	1.2/50 μs , $I_{PP} = -53\text{ A}$, $R_S = 47\ \Omega$, $V_{GG} = -48\text{ V}$, $C_G = 220\text{ nF}$		0.1		μC
C_{KA} Cathode-anode off-state capacitance	$f = 1\text{ MHz}$, $V_d = 1\text{ V}$, $I_G = 0$, (see Note 3)	$V_D = -3\text{ V}$		100	pF
		$V_D = -48\text{ V}$		50	pF

NOTES: 3. These capacitance measurements employ a three terminal capacitance bridge incorporating a guard circuit. The unmeasured device terminals are a.c. connected to the guard terminal of the bridge.

Thermal Characteristics

Parameter	Test Conditions	Min	Typ	Max	Unit
$R_{\theta JA}$ Junction to free air thermal resistance	$T_A = 25^\circ\text{C}$, EIA/JESD51-3 PCB, EIA/JESD51-2 environment, $P_{TOT} = 1.7\text{ W}$ D Package			120	$^\circ\text{C/W}$

Parameter Measurement Information



PM6XAAC

Figure 1. Voltage-Current Characteristic
 Unless Otherwise Noted, All Voltages are Referenced to the Anode

Thermal Information

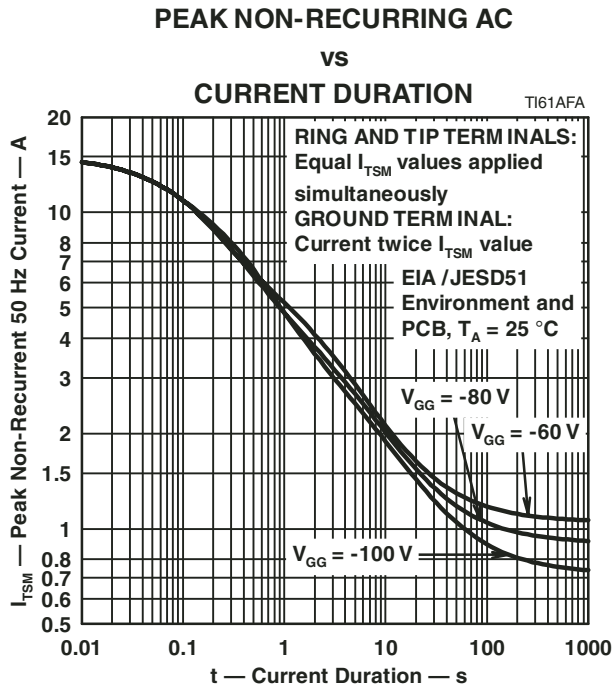


Figure 2. Non-repetitive Peak On-State Current against Duration
 (Gate Voltage Ranges are -20 V to -75 V for the '61089 and -20 V to -100 V for the '61089A)

APPLICATIONS INFORMATION

Application Circuit (Continued)

protector. The TISP7xxxF3 protector has the same protection voltage for any terminal pair. This protector is used when the ring generator configuration may be ground or battery-backed. For dedicated ground-backed ringing generators, the TISP3xxxF3 gives better protection as its inter-conductor protection voltage is twice the conductor to ground value.

Relay contacts 3a and 3b connect the line conductors to the SLIC via the '61089 protector. The protector gate reference voltage comes from the SLIC negative supply (V_{BAT}). A 220 nF gate capacitor sources the high gate current pulses caused by fast rising impulses.

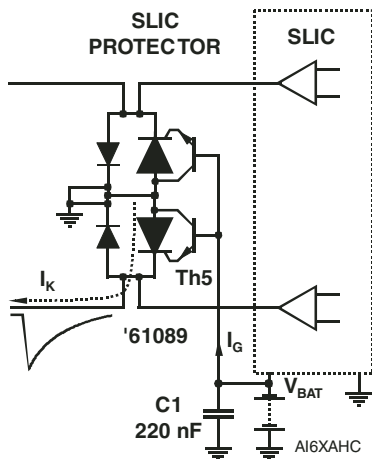


Figure 4. Negative Overvoltage Condition

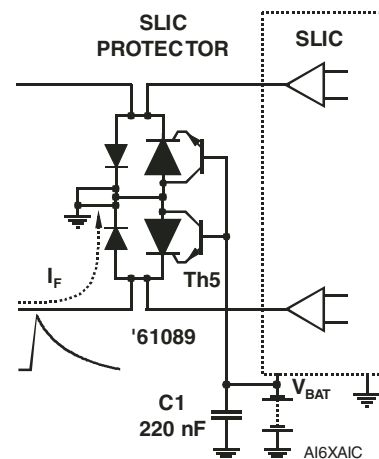


Figure 5. Positive Overvoltage Condition

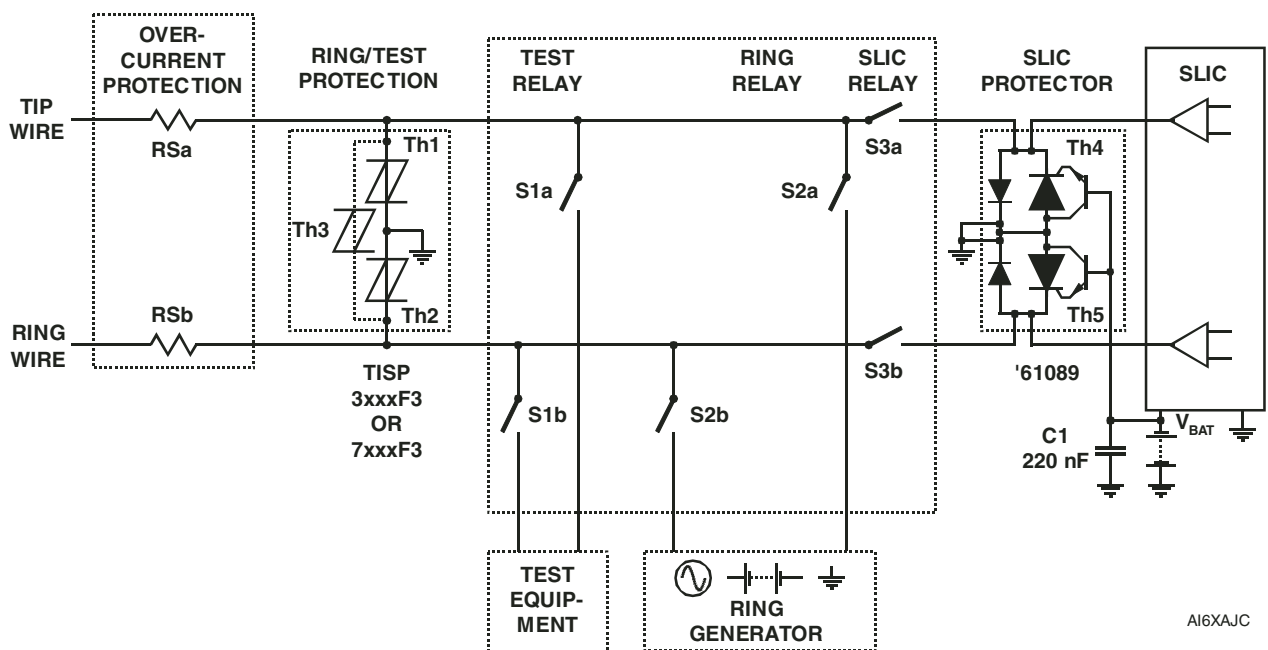


Figure 6. Typical Application Circuit

TISP61089 Gated Protector Series

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MECHANICAL DATA

Device Symbolization Code

Devices will be coded as below.

Device	Symbolization Code
TISP61089D	P61089
TISP61089SD	61089S
TISP61089AD	61089A
TISP61089ASD	1089AS

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